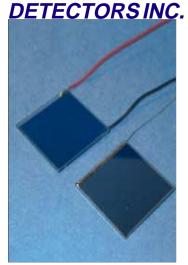
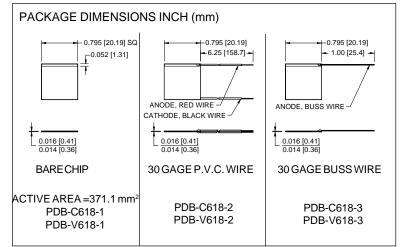
PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C618 Photovoltaic Type PDB-V618





FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

DESCRIPTION: Low cost blue enhanced planar diffused silicon solderable photodiode. The **PDB-V618** cell is designed for low noise, photovoltaic applications. The **PDB-C618** cell is designed for low capacitance, high speed, photoconductive

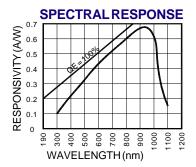
operation. They are available bare, PVC or buss wire leads.

APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	PDB-	C618	PDB-	V618	UNITS	
OTWIDGE		MIN	MAX	MIN	MAX	Oraro	
VBR	Reverse Voltage		75		25	V	
T _{STG}	Storage Temperature	-40	+125	-40	+125	°C	
То	Operating Temperature Range	-40	+100	-40	+100	°C	
Ts	Soldering Temperature		+224		+224	°C	
I	Light Current		500		500	mA	



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	PDB-C618			PDB-V618			LINUTO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	3.5	4.0		3.0	3.4		mA
ΙD	Dark Current	H = 0, V _R = 5 V*		30	500		20	500	nA
Rsн	Shunt Resistance	H = 0, V _R = 10 mV	.10	1.5		.15	2		Ω M
TC RsH	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8			-8		%/°C
CJ	Junction Capacitance	H = 0, V _R = 5 V**		2000			45000		pF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
VBR	Breakdown Voltage	I = 10 m A	27	50		.5	10		V
NEP	Noise Equivalent Power	V _R = 0 V @ Peak	5.5 10 ⁻¹³ TYP		1.5 x 10 ⁻¹⁴ TYP			W/ √Hz	
tr	Response Time	RL = 1 KΩ V _R = 5 V**		200			4000		nS

^{*}VR = 100 mV on Photovoltaic type **VR = 0 V on Photovoltaic type